BUK125-50L

DESCRIPTION

Monolithic logic level protected power MOSFET using **TOPFET2** technology assembled in a 5 pin surface mounting plastic package.

APPLICATIONS

General purpose switch for automotive systems and other applications.

FEATURES

- TrenchMOS output stage with low on-state resistance
- Separate input pin for higher frequency drive
- 5 V logic compatible input
 Separate supply pin for logic
- and protection circuits with low operating current
- Overtemperature protection
- Drain current limiting
- Short circuit load protectionLatched overload trip state reset
- by the protection pin

 Diagnostic flag pin indicates protection supply connected, overtemperature condition,overload tripped state, or open circuit load (detected in the off-state)

- ESD protection on all pins
- Overvoltage clamping

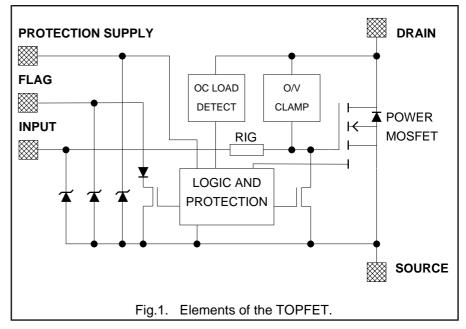
PINNING - SOT263B-01

PIN	DESCRIPTION
1	Input
2	Flag
3	Drain
4	Protection supply
5	S ource
tab	Drain

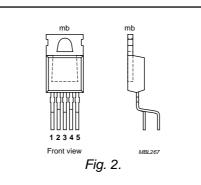
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$\begin{matrix} V_{DS} \\ I_D \\ P_{tot} \\ T_j \\ R_{DS(ON)} \end{matrix}$	Continuous drain source voltage Continuous drain current Total power dissipation Continuous junction temperature Drain-source on-state resistance	50 40 107 150 20	V A W °C mΩ
SYMBOL	PARAMETER	NOM.	UNIT
V _{PS}	Protection supply voltage	5	V

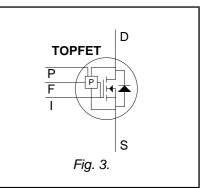
FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



SYMBOL



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LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
	Continuous voltage				
V _{DS}	Drain source voltage ¹	$V_{IS} = 0 V$	-	50	V
	Continuous currents				
I _D	Drain current	$V_{PS} = 5 V; T_{mb} = 25^{\circ}C$	-	self - limited	А
l _i I _F I _P	Input current Flag current Protection supply current	$V_{PS} = 0 V; T_{mb} = 80^{\circ}C$	- -5 -5 -5	40 5 5 5	A mA mA mA
	Thermal				
P _{tot}	Total power dissipation	$T_{mb} = 25^{\circ}C$	-	107	W
T _{stg} Tj T _{sold}	Storage temperature Junction temperature ² Mounting base temperature	continuous during soldering	-55 - -	175 150 260	ပံံပံ

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _c	5 1	Human body model; C = 250 pF; R = 1.5 k Ω	-	2	kV

OVERLOAD PROTECTION LIMITING VALUE

With an adequate protection supply connected, TOPFET can protect itself from two types of overload overtemperature and short circuit load. For overload conditions an n-MOS transistor turns on between the input and source to quickly discharge the power MOSFET gate capacitance.

The drain current is limited to reduce dissipation in case of short circuit load. Refer to OVERLOAD CHARACTERISTICS.

SYMBOL	PARAMETER	REQUIRED CONDITION	MIN.	MAX.	UNIT
	Overload protection ³	protection supply			
V _{DS}	Drain source voltage	$V_{PS} \ge 4 V$	0	35	V

OVERVOLTAGE CLAMPING LIMITING VALUES

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
	Inductive load turn off	I_{DM} = 25 A; $V_{DD} \le 20$ V			
E _{DSM}	Non-repetitive clamping energy	$T_{mb} = 25^{\circ}C$	-	550	mJ
E _{DRM}	Repetitive clamping energy	T _{mb} ≤ 95°C; f = 250 Hz	-	60	mJ

¹ Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.

² A higher T_j is allowed as an overload condition but at the threshold $T_{j(TO)}$ the over temperature trip operates to protect the switch.

³ All control logic and protection functions are disabled during conduction of the source drain diode. If the protection circuit was previously latched, it would be reset by this condition.

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THERMAL CHARACTERISTIC

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Thermal resistance					
R _{th j-mb}	Junction to mounting base	-	-	0.94	1.17	K/W

OUTPUT CHARACTERISTICS

Limits are for -40°C \leq T_{mb} \leq 150°C; typicals are for T_{mb} = 25°C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Off-state	$V_{IS} = 0 V$				
V _{(CL)DSS}	Drain-source clamping voltage	$I_{D} = 10 \text{ mA}$	50	-	70	V
		$I_{\text{DM}} = 5 \text{ A}; \text{ tp} \leq 300 \mu\text{s}; \delta \leq 0.01$	50	60	70	V
I _{DSS}	Drain source leakage current ¹	$V_{PS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$ $T_{mb} = 25^{\circ}\text{C}$	-	- 0.1	100 10	μΑ μΑ
	On-state	$t_p \le 300 \ \mu s; \ \delta \le 0.01; \ V_{PS} \ge 4 \ V$				
R _{DS(ON)}	Drain-source resistance	$I_{DM} = 15 \text{ A}; V_{IS} \ge 4.4 \text{ V}$	-	-	40	mΩ
. ,		$T_{mb} = 25^{\circ}C$	-	15	20	mΩ

INPUT CHARACTERISTICS

Limits are for -40°C \leq T_{mb} \leq 150°C; typicals are for T_{mb} = 25°C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Normal operation					
$V_{\text{IS(TO)}}$	Input threshold voltage ²	$I_{D} = 1 \text{ mA}$ $T_{mb} = 25^{\circ}\text{C}$	0.6 1.1	- 1.6	2.6 2.1	V V
I _{IS}	Input current	$V_{IS} = 5 V$	-	16	100	μA
V _{(CL)IS}	Input clamping voltage	I ₁ = 1 mA	5.5	6.4	8.5	V
R _{IG}	Internal series resistance ³	to gate of power MOSFET	-	1.7	-	kΩ
	Overload protection latched	$V_{PS} \ge 4 V$				
I _{ISL}	Input current	$V_{IS} = 5 V$	1	2.7	4	mA

¹ The drain current required for open circuit load detection is switched off when there is no protection supply, in order to ensure a low off-state quiescent current. Refer to OPEN CIRCUIT LOAD DETECTION CHARACTERISTICS.

² The measurement method is simplified if $V_{PS} = 0$ V, in order to distinguish I_D from I_{DSP} . Refer to OPEN CIRCUIT LOAD DETECTION CHARACTERISTICS.

 $^{{\}bf 3}$ This is not a directly measurable parameter.

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PROTECTION SUPPLY CHARACTERISTICS

Limits are for -40 $^\circ\text{C} \leq T_{mb} \leq 150 \,^\circ\text{C};$ typicals are for T_{mb} = 25 $^\circ\text{C}.$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Protection & detection					
V_{PSF}	Threshold voltage ¹	$I_{F} = 100 \ \mu A; \ V_{DS} = 5 \ V$	2.5	3.45	4	V
I _{PS} , I _{PSL}	Normal operation or protection latched Supply current	V _{PS} = 4.5 V	-	210	450	μA
V _{(CL)PS}	Clamping voltage	I _P = 1.5 mA	5.5	6.5	8.5	V
(): -	Overload protection latched					
V _{PSR} t _{pr}	Reset voltage Reset time	$V_{PS} \le 1 V$	1 10	1.8 45	3 120	V μs

OPEN CIRCUIT LOAD DETECTION CHARACTERISTICS

An open circuit load condition can be detected while the TOPFET is in the off-state. Refer to TRUTH TABLE. $V_{PS} = 5 \text{ V}$. Limits are for -40°C $\leq T_{mb} \leq 150$ °C and typicals are for $T_{mb} = 25$ °C.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{DSP}	Off-state drain current ²	$V_{IS} = 0 V; 2 V \le V_{DS} \le 40 V$	0.9	1.8	2.7	mA
V _{DSF}	Drain threshold voltage ³	$V_{IS} = 0 V$	0.2	1	2	V
V _{ISF}	Input threshold voltage ⁴	I _D = 100 μA	0.3	0.8	1.1	V

OVERLOAD CHARACTERISTICS

 $T_{mb} = 25^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Short circuit load protection	V _{PS} > 4 V				
I _D	Drain current limiting⁵	$V_{\text{IS}} = 5 \text{ V}; \qquad -40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$	40	62	84	Α
P _{D(TO)}	Overload power threshold	for protection to operate	90	220	330	W
T _{DSC}	Characteristic time	which determines trip time ⁶	250	500	700	μs
	Overtemperature protection	V _{PS} = 5 V				
$T_{j(TO)}$	Threshold temperature	from $I_D \ge 4$ A or $V_{DS} > 0.2$ V	150	170	-	°C

¹ When V_{PS} is less than V_{PSF} the flag pin indicates low protection supply voltage. Refer to TRUTH TABLE.

² The drain source current which flows in a normal load when the protection supply is high and the input is low.

³ If $V_{DS} < V_{DSF}$ then the flag indicates open circuit load.

⁴ For open circuit load detection, V_{IS} must be less than $V_{\text{ISF}}.$

⁵ Product specification will include curve showing output characteristics.

⁶ Trip time $t_{d sc}$ varies with overload dissipation P_D according to the formula $t_{d sc} \sim T_{DSC} / In[P_D / P_{D(TO)}]$.

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TRUTH TABLE

For normal, open-circuit load and overload conditions or inadequate protection supply voltage. Assumes proper external pull-up for flag pin. Refer to FLAG CHARACTERISTICS.

1	1	0		
	•	0 ON		
1	0	0	OFF	
1	1	0	ON	
1	0	1	OFF	
1	1	1	OFF	
1	Х	1	OFF	
0	1	1	ON	
0	0	1	OFF	
		1 1 1 0 1 1 1 1 1 1 1 1 1 1 1 1 0 1 0 0	1 1 0 1 1 0 1 0 1 1 1 1 1 X 1 0 1 1 0 1 1 0 1 1	

KEY '0' equals low '1' equals high 'X' equals don't care.

FLAG CHARACTERISTICS

The flag is an open drain transistor which requires an external pull-up circuit. Limits are for -40°C $\leq T_{mb} \leq 150$ °C; typicals are for $T_{mb} = 25$ °C.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Flag 'low'	normal operation; $V_{PS} = 5 V$				
V _{FSF}	Flag voltage	I _F = 100 μA	-	0.8	1	V
I _{FSF}	Flag saturation current	$V_{FS} = 5 V$	-	10	-	mA
	Flag 'high'	overload or fault				
I _{FSO}	Flag leakage current	$V_{FS} = 5 V$	-	0.1	10	μA
V _{(CL)FS}	Flag clamping voltage	I _F = 100 μA	5.5	6.2	8.5	V
	Application information					
R _F	Suitable external pull-up resistance	$V_{FF} = 5 V$	-	47	-	kΩ

SWITCHING CHARACTERISTICS

 $T_{\text{mb}} = 25^{\circ}\text{C}; \ \text{R}_{\text{I}} = 50 \ \Omega; \text{R}_{\text{IS}} = 50 \ \Omega; \text{V}_{\text{DD}} = 15 \text{ V}; \text{ resistive load } \text{R}_{\text{L}} = 10 \ \Omega.$

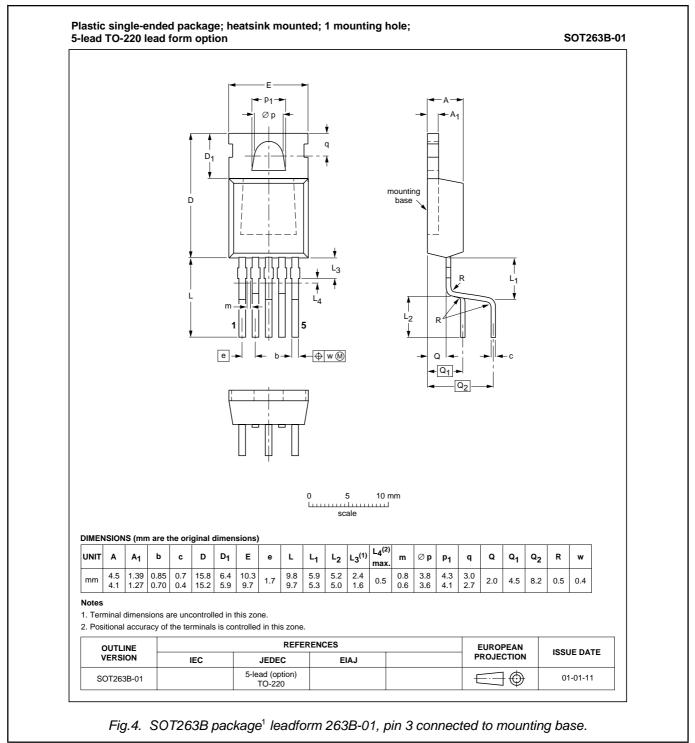
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t _{d on}	Turn-on delay time	$V_{IS}: 0 V \Rightarrow 5 V$	-	1.8	5	μs
t _r	Rise time		-	3.5	8	μs
t _{d off}	Turn-off delay time $V_{IS}: 5 V \Rightarrow 0 V$		-	11	30	μs
t _f	Fall time		-	5	12	μs

¹ In this condition the protection circuit is latched. To reset the latch the protection pin must be taken low. Refer to PROTECTION SUPPLY CHARACTERISTICS.

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MECHANICAL DATA



¹ Refer to mounting instructions for TO220 envelopes. Epoxy meets UL94 VO at 1/8". Net mass: 2 g

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DEFINITIONS

DATA SHEET STATUS				
DATA SHEET STATUS ¹	PRODUCT STATUS ²	DEFINITIONS		
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice		
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product		
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A		

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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